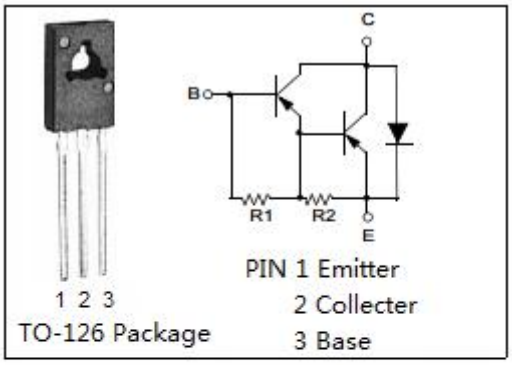
isc Silicon PNP Power Transistor — KSE700

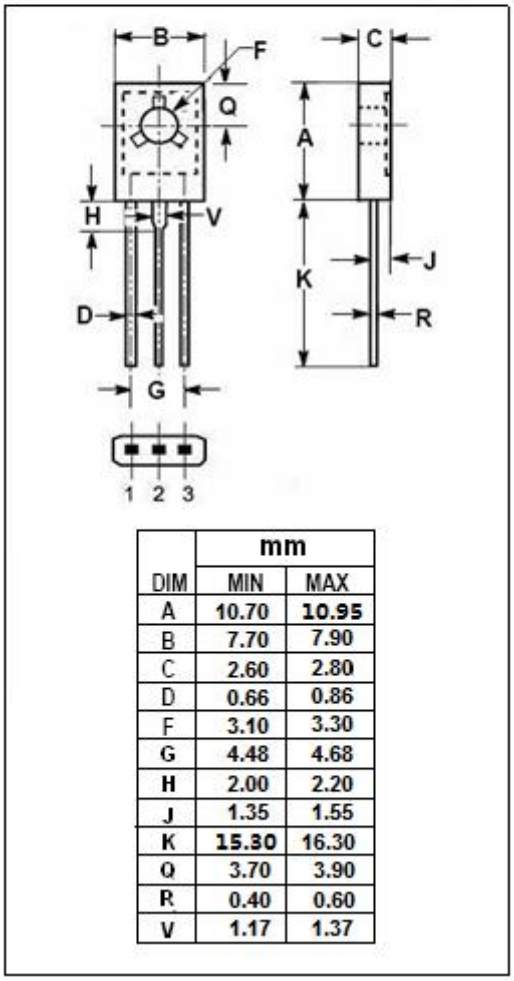


DESCRIPTION

- High DC current gain
- Low Collector Saturation Voltage
- Complement to Type KSE800
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Monolithic construction with built-in-Base-Emitter resistor



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
P_C	Collector Power Dissipation @ T_C=25℃	40	W
	Collector Power Dissipation @ T_a=25℃	2	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

isc Silicon PNP Power Transistor KSE700

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-2	mA
h_{FE-1}	DC Current Gain	I_C=- 1.5A; V_{CE}= -3V	750			
h_{FE-2}	DC Current Gain	I_C=- 4A; V_{CE}= -3V	100			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -1.5A; I_B=- 30mA			-2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -40mA			-3	V
$V_{BE(ON)-1}$	Base-Emitter On Voltage	I_C=- 1.5A; V_{CE}= -3V			-1.2	V
$V_{BE(ON)-2}$	Base-Emitter On Voltage	I_C=- 4A; V_{CE}= -3V			-3	V